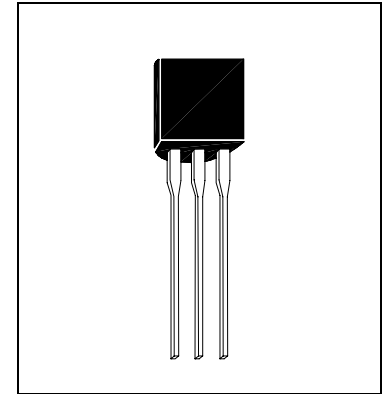




2N2907A

PNP EPITAXIAL PLANAR TRANSISTOR



Description

The 2N2907A is designed for general purpose amplifier and high speed, medium-power switching applications.

Features

- Low Collector Saturation voltage.
- High Speed Switching.
- For Complementary Use with NPN Type MPS2222A.

Absolute Maximum Ratings

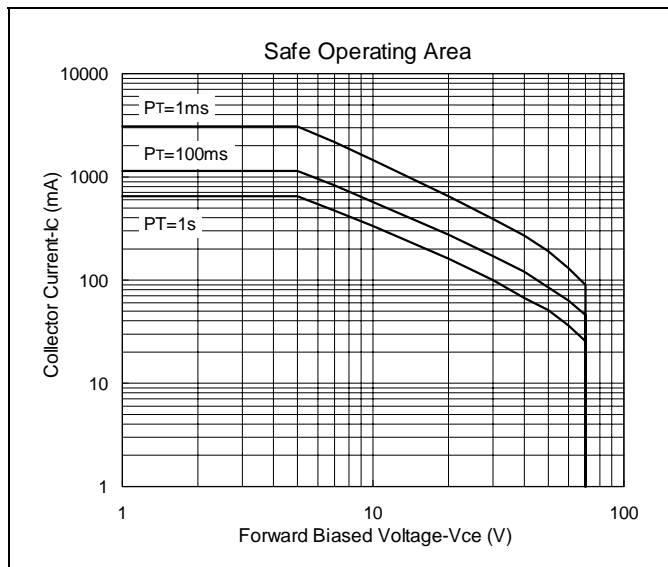
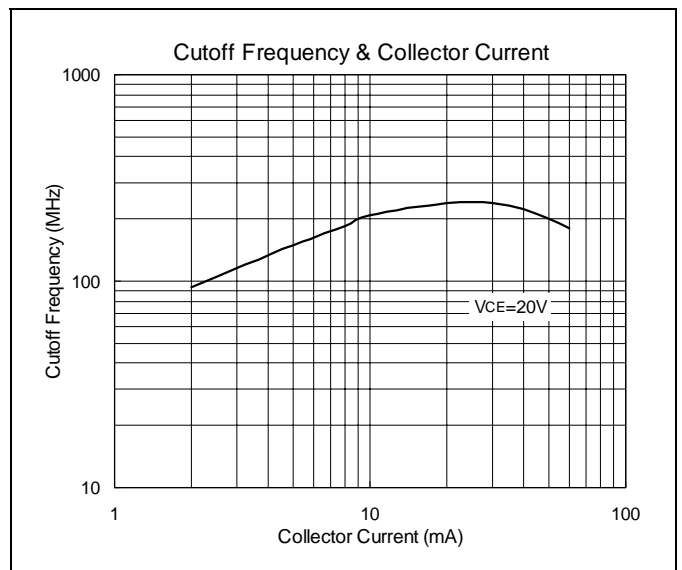
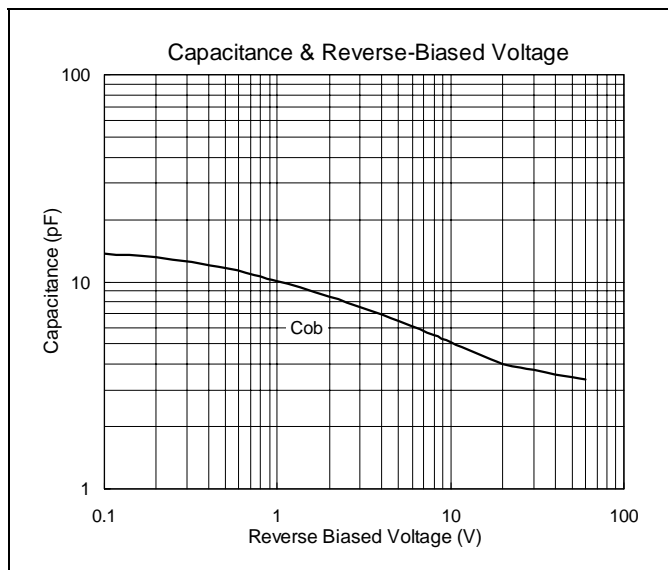
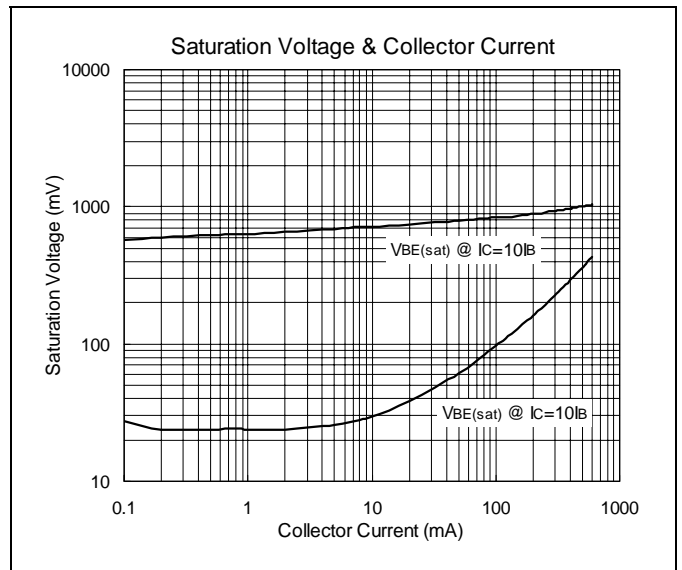
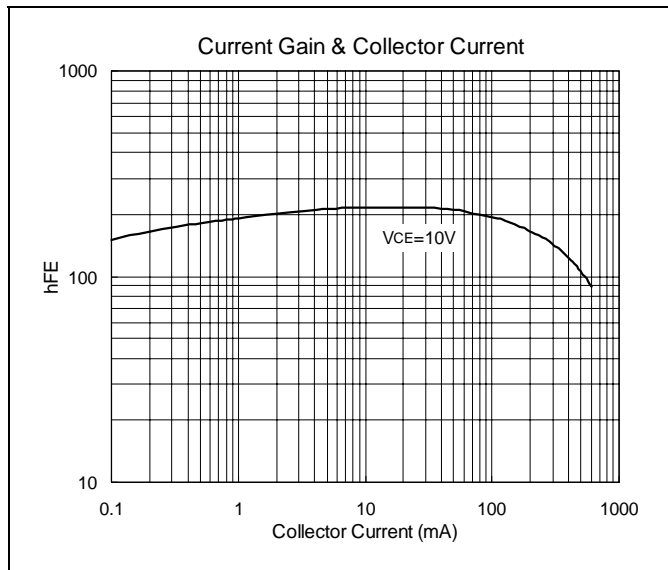
- Maximum Temperatures
 - Storage Temperature -55~+150°C
 - Junction Temperature 150 Maximum
- Maximum Power Dissipation
 - Total Power Dissipation (Ta=25°C)..... 625 mW
- Maximum Voltages and Currents (Ta=25°C)
 - VCBO Collector to Base Voltage 60 V
 - VCEO Collector to Emitter Voltage 60 V
 - VEBO Emitter to Base Voltage 5 V
 - IC Collector Current 600 mA

Characteristics (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	60	-	-	V	IC=10uA, IE=0
BVCEO	60	-	-	V	IC=10mA, IB=0
BVEBO	5	-	-	V	IC=10uA, IC=0
ICBO	-	-	10	nA	VCB=50V, IC=0
ICEX	-	-	50	nA	VCE=30V, VBE=0.5V
VCE(sat)1	-	0.2	0.4	V	IC=150mA, IB=15mA
VCE(sat)2	-	0.5	1.6	V	IC=500mA, IB=50mA
VBE(sat)1	-	-	1.3	V	IC=150mA, IB=15mA
VBE(sat)2	-	-	2.6	V	IC=500mA, IB=50mA
hFE1	75	-	-		VCE=10V, IC=100uA
hFE2	100	-	-		VCE=10V, IC=1mA
hFE3	100	-	-		VCE=10V, IC=10mA
hFE4	100	180	300		VCE=10V, IC=150mA
hFE5	50	-	-		VCE=10V, IC=500mA
fT	200	-	-	MHz	VCE=20V, IC=50mA, f=100MHz
Cob	-	-	8	pF	VCB=10V, F=1MHz

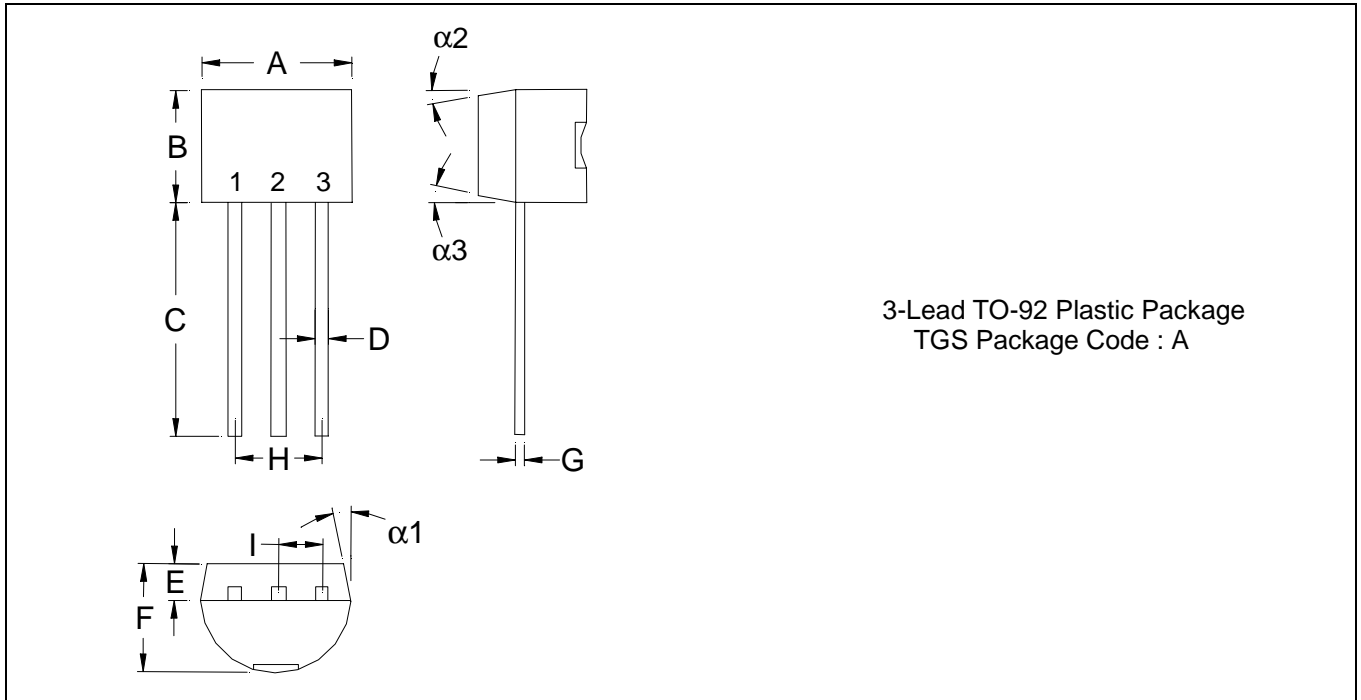


Characteristics Curve





TO-92 Dimension



*:Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1704	0.1902	4.33	4.83	G	0.0142	0.0220	0.36	0.56
B	0.1704	0.1902	4.33	4.83	H	-	*0.1000	-	*2.54
C	0.5000	-	12.70	-	I	-	*0.0500	-	*1.27
D	0.0142	0.0220	0.36	0.56	$\alpha 1$	-	*5°	-	*5°
E	-	*0.0500	-	*1.27	$\alpha 2$	-	*2°	-	*2°
F	0.1323	0.1480	3.36	3.76	$\alpha 3$	-	*2°	-	*2°